

ABSTRACT OF DISCLOSURE

A method of forming a semiconductor device is described comprising forming a first patterned conductive layer on a dielectric on a substrate. A first barrier layer comprising silicon nitride is formed on the surface of the first patterned conductive layer, followed by forming a second barrier layer comprising silicon carbide on the surface of the first barrier layer. Using standard lithographic techniques a via and a trench are formed to the surface of the conductive layer.